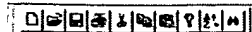


Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/673539	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:47
L2	34737	transistor with (substrate with (source drain))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:48
L3	10022	transistor with (substrate with (source drain)) same ((n p first second) near3 type)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:50
L4	2680	3 and transistor with (substrate with (source drain)) same ((first second) near3 (impurity conductivity dopant ion))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:52
L5	2604	4 and gate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:53
L6	770	5 and silicide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:54
L7	28	6 and "LDMOS"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 08:54

10/673539



## Active

- ☞ L1: (1) 10/673539
- ☞ L2: (34737) transistor with (substrate with (source drain))
- ☞ L3: (10022) transistor with (substrate with (source drain)) same ((n p first second) near3 type)
- ☞ L4: (2680) 3 and transistor with (substrate with (source drain)) same ((first second) near3 (impu...
- ☞ L5: (2604) 4 and gate
- ☞ L6: (770) 5 and silicide
- ☞ L7: (28) 6 and "LDMOS"

Search  Browse  Clear

DBs: ☒ US-PG-PUB:USPAT: B ☐ Burs

Default operator:  OR  Highlight all hit terms initially ☐

6 and "LDMOS"

BRS form ISAR form Image Text HTML

	U	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrie
1	<input type="checkbox"/>	US 20050064670 A	2005032	15	Depletion drain-extended MOS transistors and methods for	438/305		
2	<input type="checkbox"/>	US 20040262680 A	2004123	8	Dmos transistor	257/335	257/336;	
3	<input type="checkbox"/>	US 20040251517 A	2004121	192	Semiconductor device and method of manufacturing the sa	257/565	257/557;	
4	<input type="checkbox"/>	US 20040251492 A	2004121	18	LDMOS transistors and methods for making the same	257/335	257/343;	
5	<input type="checkbox"/>	US 20040241950 A	2004120	10	Method to manufacture high voltage MOS transistor by ion	438/301	257/E21.4	
6	<input type="checkbox"/>	US 20040238854 A	2004120	8	Field effect transistor	257/213	257/E29.0	
7	<input type="checkbox"/>	US 20030218209 A	2003112	13	Microwave field effect transistor structure	257/335	257/E29.2	
8	<input type="checkbox"/>	US 20030170943 A	2003091	11	Electrostatic discharge protection in double diffused MOS	438/197	361/91.6	
9	<input type="checkbox"/>	US 20030001199 A	2003010	11	Electrostatic discharge protection in double diffused MOS	257/330		
10	<input type="checkbox"/>	US 20020109184 A	2002081	14	LDMOS with improved safe operating area	257/335	257/336;	
11	<input type="checkbox"/>	US 20020033508 A	2002032	25	Semiconductor device and method for fabricating the same	257/368	257/E29.0	
12	<input type="checkbox"/>	US 20010015458 A	2001082	40	Semiconductor device having high breakdown voltage	257/335	257/E21.4	
13	<input type="checkbox"/>	US 6958515 B2	2005102	13	N-channel LDMOS with buried p-type region to prevent pa	257/341	257/331;	
14	<input type="checkbox"/>	US 6900101 B2	2005053	17	LDMOS transistors and methods for making the same	438/276	257/E21.4	
15	<input type="checkbox"/>	US 6897525 B1	2005052	31	Semiconductor device and method of manufacturing the sa	257/343	257/409;	
16	<input type="checkbox"/>	US 6855985 B2	2005021	254	Modular bipolar-CMOS-DMOS analog integrated circuit &	257/338	257/370;	

☐ Hits 
 ☐ Details 
 ☒ HTML

Ready

RUN

- L1: (1) 10/673539
- L2: (34737) transistor with (substrate with (source drain))
- L3: (10022) transistor with (substrate with (source drain)) same ((n p first second) near3 type)
- L4: (2680) 3 and transistor with (substrate with (source drain)) same ((first second) near3 (impu...
- L5: (2604) 4 and gate
- L6: (770) 5 and silicide
- L7: (28) 6 and "LDMOS"

Search [ ] Browse [ ] Clear [ ]  
DBs US-PGPUB USPAT: B ☒ Duplicates  
Default operator: OR ☐ Highlight all hit terms initially

6 and "LDMOS"

▲ BRS form ▲ ISAR form ☒ Image ☐ Text ☐ HTML

	U	Document ID	Issue Date	Page	Title	Current O	Current X	Retrieval
11	□ □	US 20020033508 A	2002032	25	Semiconductor device and method for fabricating the same	257/368	257/E29.0	
12	□ □	US 20010015458 A	2001082	40	Semiconductor device having high breakdown voltage	257/335	257/E21.4	
13	□ □	US 6958515 B2	2005102	13	N-channel LDMOS with buried p-type region to prevent pa	257/341	257/331;	
14	□ □	US 6900101 B2	2005053	17	LDMOS transistors and methods for making the same	438/276	257/E21.4	
15	□ □	US 6897525 B1	2005052	31	Semiconductor device and method of manufacturing the sa	257/343	257/409;	
16	□ □	US 6855985 B2	2005021	254	Modular bipolar-CMOS-DMOS analog integrated circuit &	257/338	257/370;	
17	□ □	US 6838731 B1	2005010	15	Microwave transistor structure having step drain region	257/343	257/288;	
18	□ □	US 6831332 B2	2004121	14	Microwave field effect transistor structure	257/343	257/344;	
19	□ □	US 6707102 B2	2004031	24	Semiconductor device including an insulated gate type field	257/340	257/328;	
20	□ □	US 6521923 B1	2003021	21	Microwave field effect transistor structure on silicon carbid	257/288	257/213;	
21	□ □	US 6506648 B1	2003011	19	Method of fabricating a high power RF field effect transisto	438/286	257/262;	
22	□ □	US 6373110 B2	2002041	38	Semiconductor device having high breakdown voltage	257/401	257/322;	
23	□ □	US 6291845 B1	2001091	11	Fully-dielectric-isolated FET technology	257/288	254/260;	
24	□ □	US 5981318 A	1999110	11	Fully-dielectric-isolated FET technology	438/162	438/218;	
25	□ □	US 5856696 A	1999010	7	Field effect transistor having dielectrically isolated sources	257/377	257/371;	
26	□ □	US 5773328 A	1998063	13	Method of making a fully-dielectric-isolated fet	438/162	257/E21.4	